

Description

The AO4884 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 40V I_D = 12A$ $R_{DS(ON)} < 16m\Omega @ V_{GS} = 10 V$ $R_{DS(ON)} < 24m\Omega @ V_{GS} = 4.5V$

Application

Battery protection Load switch

Uninterruptible power supply

Package Marking and Ordering Information

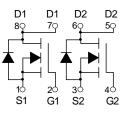
Product ID	Pack	Marking	Qty(PCS)
AO4884	SOP-8	4884 XXX YYYY	3000

Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	<u>+</u> 20	V
I₀@T₄=25℃	Drain Current, V _{GS} @ 4.5V ³	12	A
I₀@T₄=70℃	Drain Current, V _{GS} @ 4.5V ³	7	A
Ідм	Pulsed Drain Current ¹	40	A
P _D @T _A =25°C	Total Power Dissipation	2.9	W
Тятс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	65	°C/W







Dual N-Channel MOSFET



Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· · · · ·					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.5	2.0	V
Drain-Source On-State Resistance	D	V_{GS} =10V, I_{D} =8A	-	12.0	16	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I_{D} =4A	-	18.9	24	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =8A	33	-	-	S
Dynamic Characteristics (Note4)	· · ·		•			
Input Capacitance	C _{lss}		-	964	-	PF
Output Capacitance	C _{oss}	V _{DS} =20V,V _{GS} =0V, F=1.0MHz	-	109	-	PF
Reverse Transfer Capacitance	C _{rss}		-	96	-	PF
Switching Characteristics (Note 4)	· · · · ·					
Turn-on Delay Time	t _{d(on)}		-	5.5	-	nS
Turn-on Rise Time	tr	V_{DD} =20V, R _L =2.5 Ω	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	N/ 00\/ L 0A	-	22.9	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=20V, I_{D}=8A,$	-	3.5	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	5.3	-	nC
Drain-Source Diode Characteristics			·		•	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	0.8	1.2	V

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)



Typical Electrical and Thermal Characteristics (Curves)

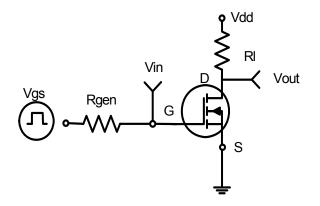


Figure 1:Switching Test Circuit

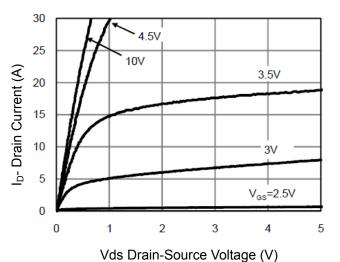
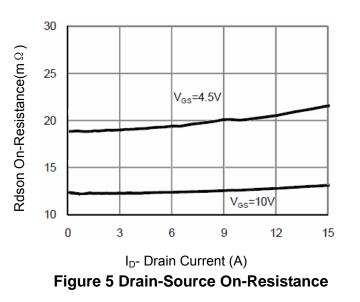


Figure 3 Output Characteristics



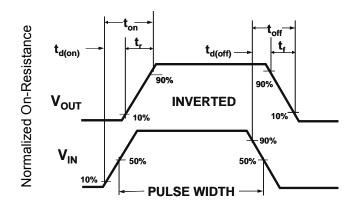


Figure 2:Switching Waveforms

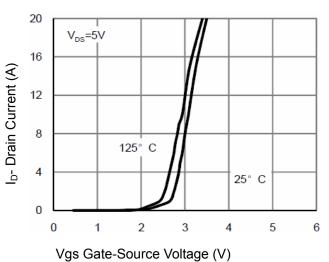


Figure 4 Transfer Characteristics

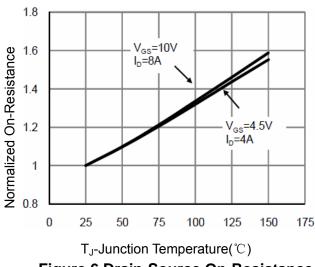
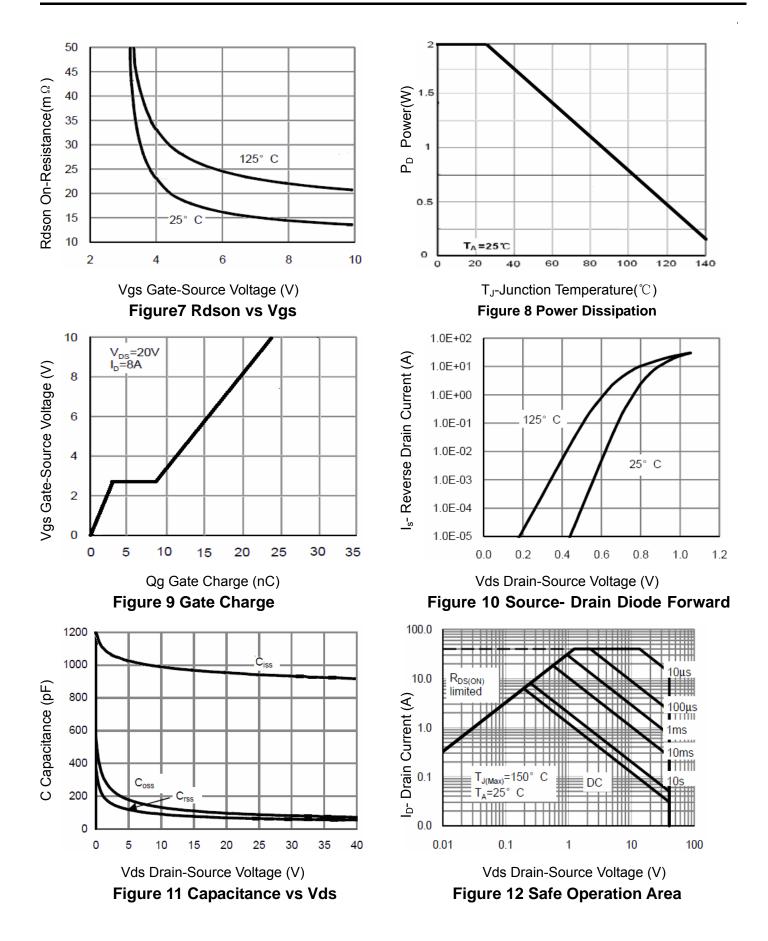
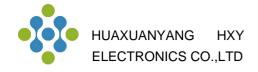


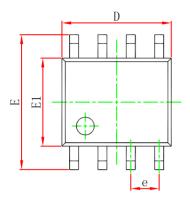
Figure 6 Drain-Source On-Resistance

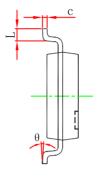


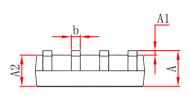




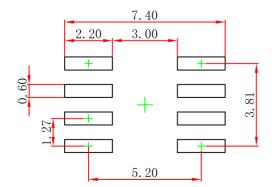
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
Α	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
с	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0 °	8°	0 °	8°



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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